

Erratum to: A Novel 2.5–3.1 GHz Wide-Band Low-Noise Amplifier in 0.18 μm CMOS

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Published online: 9 December 2014
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Erratum to: Wireless Pers Commun (2014) 79:1993–2003 DOI 10.1007/s11277-014-1969-7

There were incorrect values in the NF column in Table 2 of the original publication. The corrected Table 2 is shown below.

Table 2 Performance summary

Ref.	BW (GHz)	S11 (dB)	Power gain (dB)	NF (dB)	Power (mW)	Technology
[9]	3–8	< −8	15.2	3.14–6.28	3.77	0.18 μm
[10]	2.8–10.4	< −10.1	8.4–10.4	4–6	2.15	0.18 μm
[11]	0.6–22	< −8	8.1	4.3	52	0.18 μm
[12]	4.5–6.2	< −9	13.2	4.5–6.2	23	0.18 μm
[13]	2–6.5	< −10	11.9	4.1	27	0.18 μm
[15]	3–4.8	< −10	15	Average = 3.5	5	0.18 μm
[16]	3–5	< −10	11.31	2.58–3.52	49	0.18 μm
[17]	3.1–10	< −11	14.2	< 4.8	14.5	0.18 μm
[18]	3.1–10.6	< −9.4	9.3	4.2–8	9	0.18 μm
This work	2.5–3.1	< −11.6	15.9	3.5	54.6	0.18 μm TSMC Mosis

The online version of the original article can be found under doi:[10.1007/s11277-014-1969-7](https://doi.org/10.1007/s11277-014-1969-7).

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